

AMENDMENTS TO THE CLAIMS

1. (CURRENTLY AMENDED) An erasable and programmable non-volatile cell, comprising
- a first transistor having a source, a drain and a gate;
 - a floating capacitor having a floating gate and a control gate, said floating gate being connected to said gate of said first transistor; and
 - ~~means~~ circuitry for detecting ~~to detect~~ the state, whether erased or programmed, of the cell;

said circuitry for detecting ~~characterized in that said means to detect~~ the state of the cell comprises a second transistor having a source, a drain and a gate, said second transistor being complementary to said first transistor and said gate of said second transistor being connected to said floating gate; said floating gate and the gates of said first and second transistors are embodied as single polymer layer.

2. (PREVIOUSLY AMENDED) The cell according to claim 1, characterized in that said first transistor is an n-channel transistor and said second transistor is a p-channel transistor.
3. (PREVIOUSLY AMENDED) The cell according to claim 2, characterized in that said first and second transistors are MOSFET transistors.
4. (PREVIOUSLY AMENDED) The cell according to claim 1, characterized in that the n-well diffusion region of said p-channel transistor is the control gate of said floating capacitor.
5. (CANCELLED)
6. (CANCELLED)
7. (CANCELLED)
8. (CANCELLED)